Product data sheet

1. General description

Dual ultrafast power diode in a SOT1259 (3-lead TO-3P) plastic package.

2. Features and benefits

- Very low on-state loss
- Fast switching
- Soft recovery characteristic minimizes power consuming oscillations
- High reverse surge capability
- High thermal cycling performance
- Low thermal resistance

3. Applications

Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	200	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 119 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	15	Α
Static characte	eristics					
V _F	forward voltage	I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	0.78	0.9	V
Dynamic chara	acteristics					,
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	18	25	ns





5. Pinning information

Table 2. Pinning information

Pin S	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		A1
2	K	cathode	10000	
3	A2	anode 2		K sym125
mb	mb	mounting base; connected to cathode	TO3P (SOT1259)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYQ72EK-200	ТОЗР	Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO3P	SOT1259			

7. Marking

Table 4. Marking codes

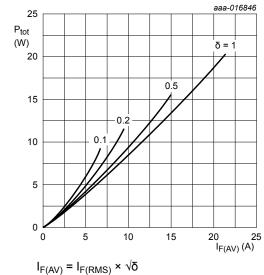
Type number	Marking code
BYQ72EK-200	BYQ72EK-200

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	200	V
V_{RWM}	crest working reverse voltage		-	200	V
V_R	reverse voltage	DC	-	200	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 119 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	15	А
I _{O(AV)}	average output current	δ = 0.5; T _{mb} ≤ 119 °C; square-wave pulse; both diodes conducting	-	30	А
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; per diode; <u>Fig. 4</u>	-	200	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	220	А
I _{RRM}	repetitive peak reverse current	t_p = 2 µs; per diode; δ = 0.001	-	0.2	Α
I _{RSM}	non-repetitive peak reverse current	t_p = 100 µs; per diode	-	0.2	А
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C
Electrostatic	discharge				
V _{ESD}	electrostatic discharge voltage	C = 250 pF; R = 1.5 kΩ; HBM	-	8	V



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ V_o = 0.79 V; R_s = 0.008 Ω

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

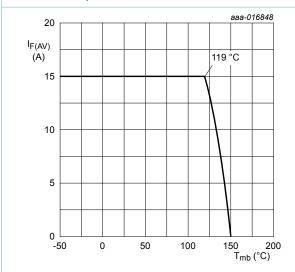
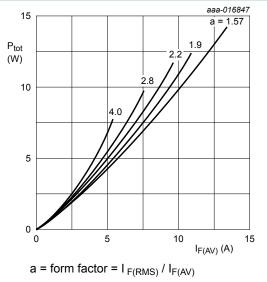


Fig. 3. Average forward current as a function of mounting base temperature; per diode; maximum values



 $V_o = 0.79 \; V; \; R_s = 0.008 \; \Omega$ Fig. 2. Forward power dissipation as a function of

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

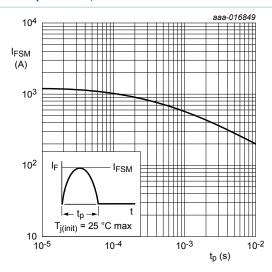


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; per diode; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)} thermal resistance from junction to mounting base	from junction to	with heatsink compound; per diode; Fig. 5	-	1.1	2	K/W
	with heatsink compound; both diodes conducting	-	0.7	1.2	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	45	-	K/W

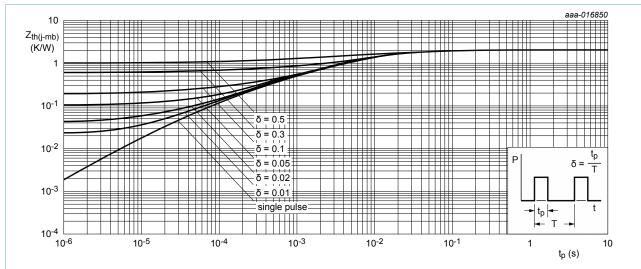


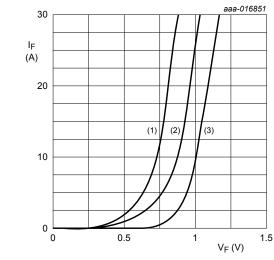
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; per diode; maximum values

10. Characteristics

Table 7. Characteristics

characteristics are per diode unless otherwise stated

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			,
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	1	1.2	V
		I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	0.95	1.05	V
		I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	0.78	0.9	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	3	20	μA
		V _R = 600 V; T _j = 100 °C	-	0.3	1	mA
Dynamic cl	haracteristics		1	'		,
Q _r recovered cl	recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	6	15	nC
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$	-	10	-	nC
t _{rr}	reverse recovery time	T _j = 25 °C; <u>Fig. 7</u>	-	18	25	ns
I _{RM}	peak reverse recovery current		-	1	-	Α
V_{FRM}	forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 8	-	1	-	V



 $V_0 = 0.79 \text{ V}; R_s = 0.008 \Omega$

(1) T_i = 150 °C; typical values

(2) T_i = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage, per diode

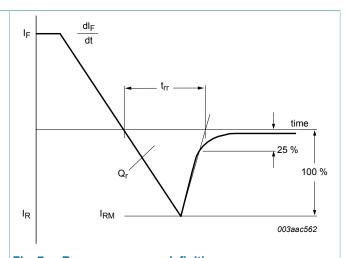
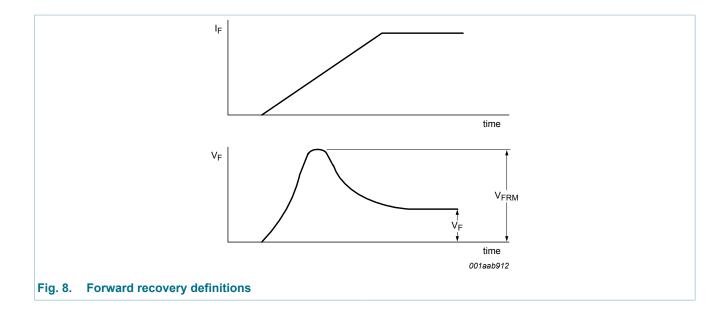


Fig. 7. Reverse recovery definitions; ramp recovery



11. Package outline

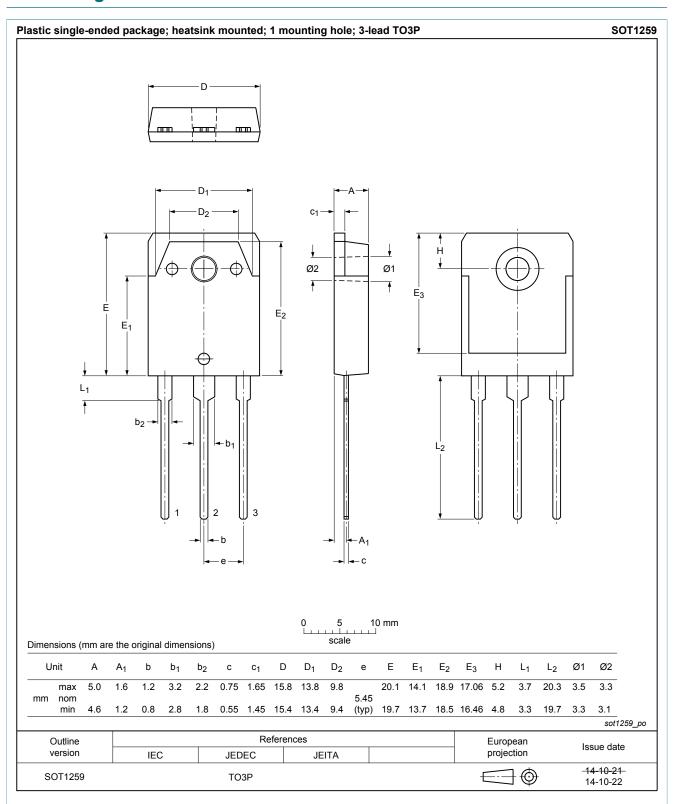


Fig. 9. Package outline TO3P (SOT1259)

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